

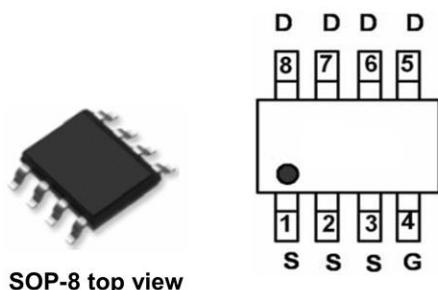
GENERAL FEATURES

- $V_{DS} = 30V, I_D = 12A$
- $R_{DS(ON)} < 12m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 16m\Omega @ V_{GS}=4.5V$

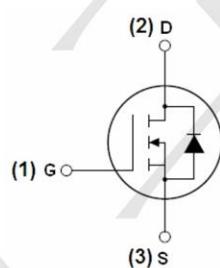
Application

- Battery protection
- Load switch

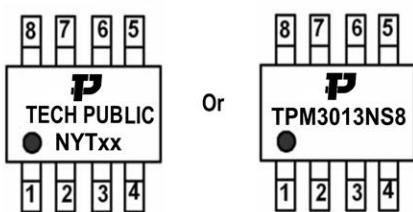
Package and Pin Configuration



Circuit diagram



Marking:



“NYT” is Part number,fixed

“xx” is internal code

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	12	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	6	A
Pulsed Drain Current	I_{DM}	50	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

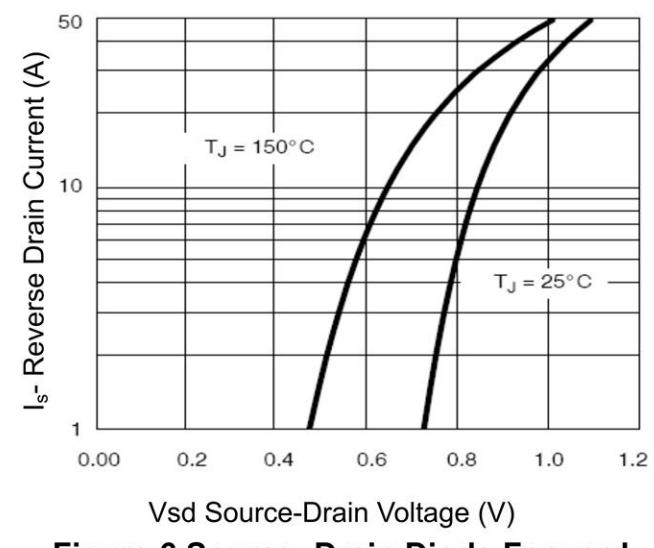
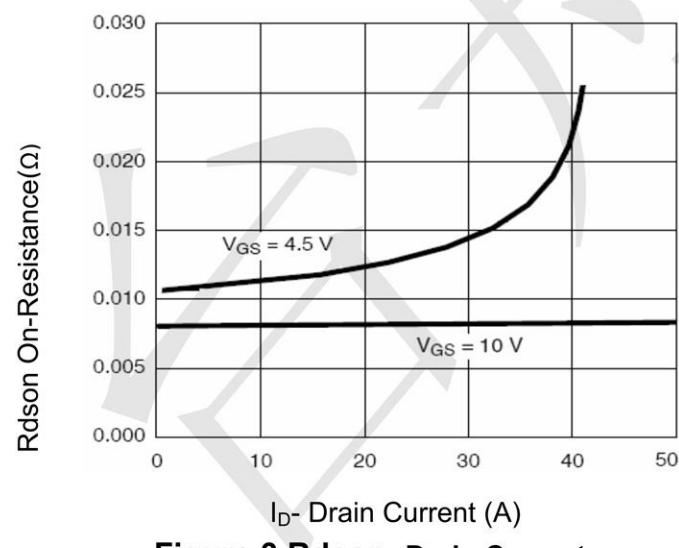
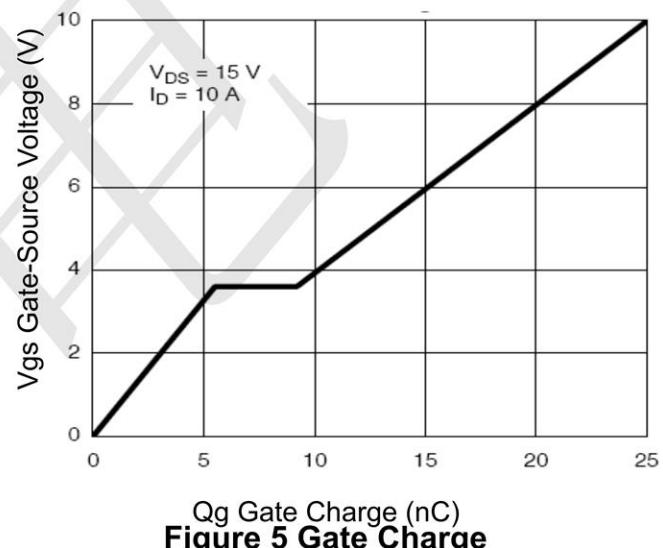
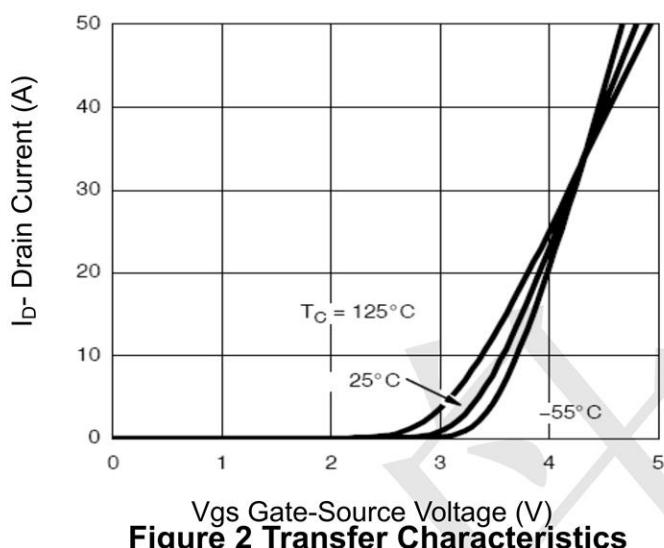
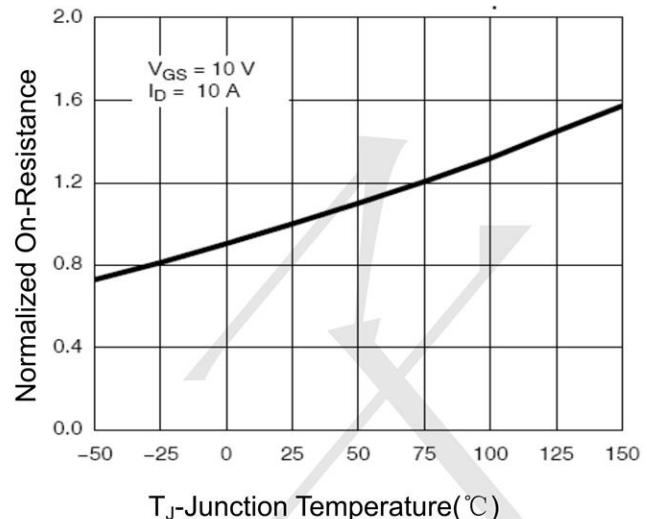
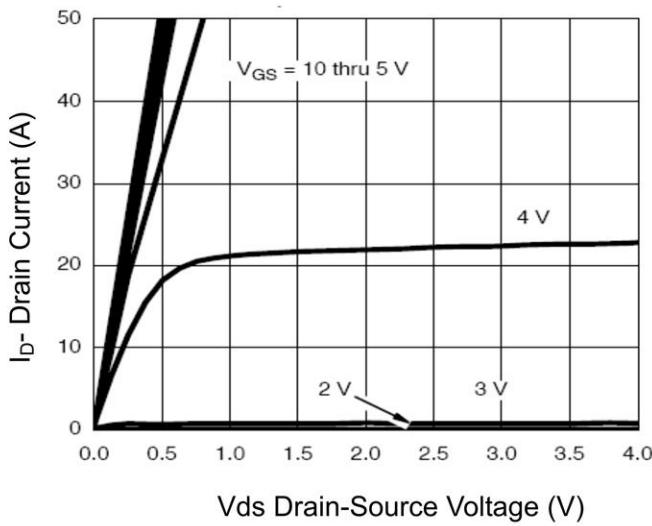
Thermal Characteristic

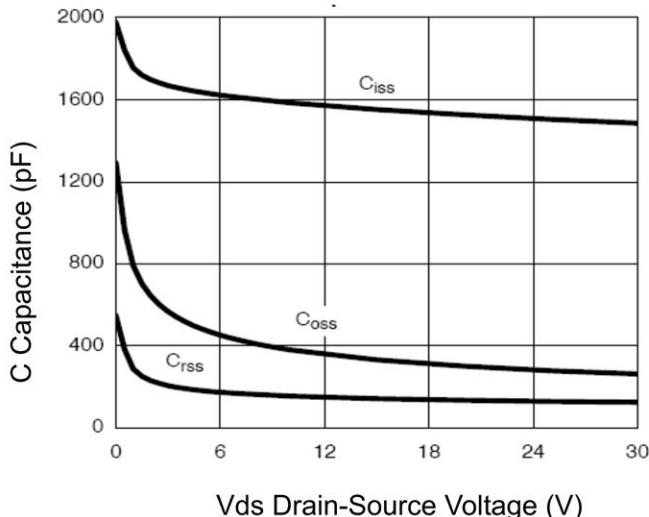
Thermal Resistance,Junction-to-Case ^(Note 2)	$R_{\theta JC}$	50	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=10\text{A}$	-	8	12	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=8\text{A}$	-	11	16	
Forward Transconductance	g_{FS}	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=10\text{A}$	15	-	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C_{iss}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	1550	-	PF
Output Capacitance	C_{oss}		-	300	-	PF
Reverse Transfer Capacitance	C_{rss}		-	180	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=25\text{V}, I_{\text{D}}=1\text{A}$ $V_{\text{GS}}=10\text{V}, R_{\text{GEN}}=6\Omega$	-	30	-	nS
Turn-on Rise Time	t_r		-	20	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	100	-	nS
Turn-Off Fall Time	t_f		-	80	-	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=10\text{A}, V_{\text{GS}}=5\text{V}$	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	5.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=10\text{A}$	-	-	1.2	V
Diode Forward Current <small>(Note 2)</small>	I_{s}		-	-	12	A

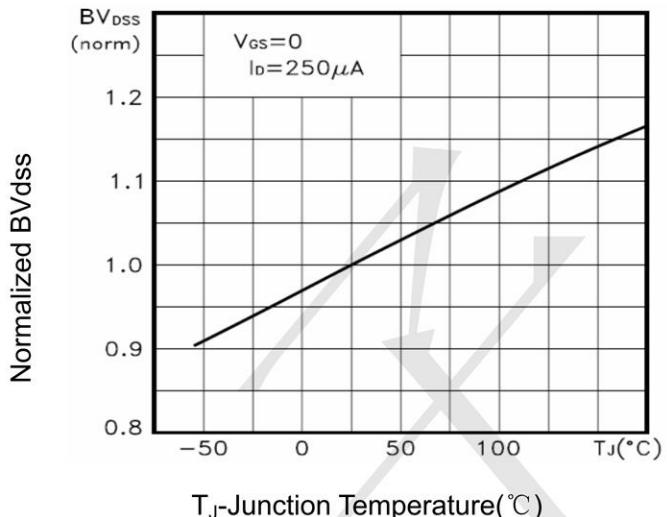
Typical Electrical and Thermal Characteristics (Curves)





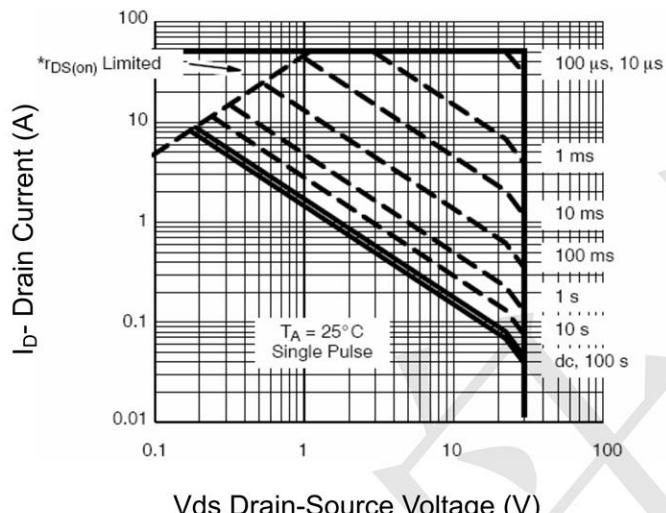
V_{ds} Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



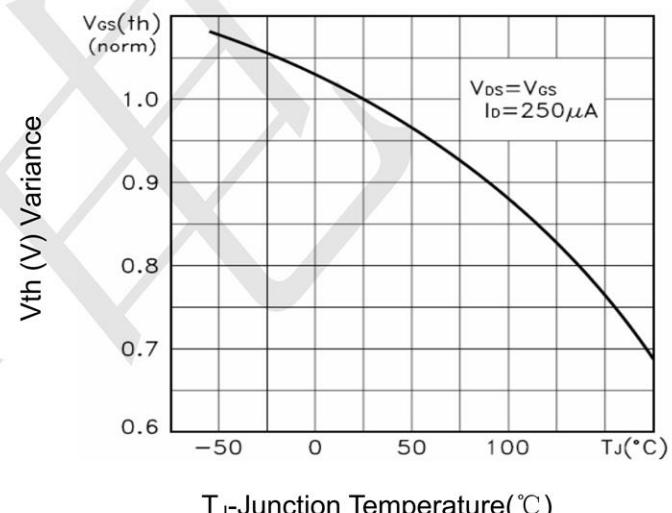
T_J -Junction Temperature(°C)

Figure 9 BV_{DSS} vs Junction Temperature



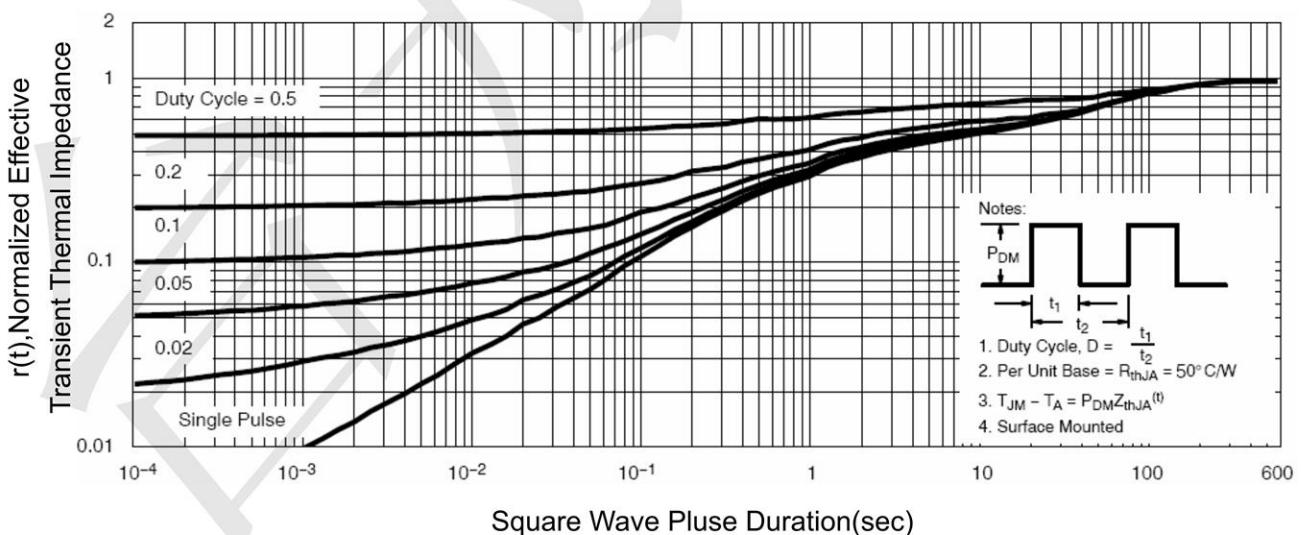
V_{ds} Drain-Source Voltage (V)

Figure 8 Safe Operation Area



T_J -Junction Temperature(°C)

Figure 10 $V_{GS(th)}$ vs Junction Temperature



Square Wave Pulse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



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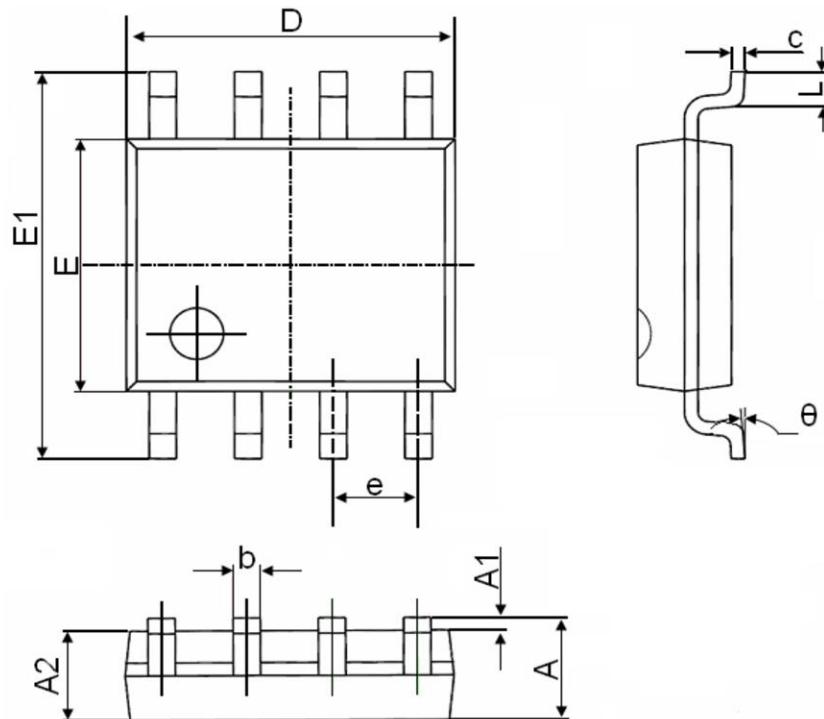
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TPM3013NS8

N-Channel Enhancement Mode Power MOSFET

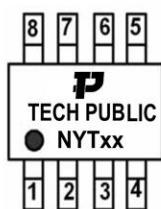
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SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking:



“P” is TECHPUBLIC LOGO

“NYT” is Part number,fixed

“xx”is internal code

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